# BLC8G27LS-60AV; BLC8G27LS-60AVH

**Power LDMOS transistor** 

**AMPLEON** 

Rev. 4 — 2 December 2016

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

60 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2300 MHz to 2690 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in the Doherty demo board.

| Test signal      | f            | V <sub>DS</sub> | P <sub>L(AV)</sub> | Gp   | $\eta_{D}$ | ACPR           |
|------------------|--------------|-----------------|--------------------|------|------------|----------------|
|                  | (MHz)        | (V)             | (W)                | (dB) | (%)        | (dBc)          |
| 1-carrier W-CDMA | 2496 to 2690 | 28              | 7                  | 15.2 | 47         | -30 <u>[1]</u> |
| IS-95            | 2300 to 2400 | 26              | 7                  | 13.6 | 48         | -30 <u>[1]</u> |

<sup>[1]</sup> Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

RF power amplifier for LTE base stations and multi carrier applications in the 2300 MHz to 2690 MHz frequency range

## 2. Pinning information

Table 2. Pinning

| Pin     | Description             | Simplified outline | Graphic symbol |
|---------|-------------------------|--------------------|----------------|
| BLC8G27 | LS-60AV (SOT1275-3)     |                    |                |
| 1       | drain1 (main)           |                    |                |
| 2       | drain2 (peak)           | 5 1 2 6            | 5   1,5<br>]   |
| 3       | gate1 (main)            |                    | <sup>/</sup>   |
| 4       | gate2 (peak)            | 7                  | 7              |
| 5       | video decoupling (main) |                    | 4              |
| 6       | video decoupling (peak) | 3 4                | 2.6            |
| 7       | source                  | [1]                | aaa-007731     |
| BLC8G27 | LS-60AVH (SOT1275-1)    |                    |                |
| 1       | drain1 (main)           |                    |                |
| 2       | drain2 (peak)           | 5 1 2 6            | 3   1,5<br>]   |
| 3       | gate1 (main)            |                    | /              |
| 4       | gate2 (peak)            | 7                  | 7              |
| 5       | video decoupling (main) |                    | 4              |
| 6       | video decoupling (peak) | 3 4                | 2.6            |
| 7       | source                  | [1]                | aaa-007731     |

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

| Type number     | Packag | Package   |           |  |  |  |  |
|-----------------|--------|---|-----------|--|--|--|--|
|                 | Name   | Description   | Version   |  |  |  |  |
| BLC8G27LS-60AV  | -      | air cavity plastic earless flanged package; 6 leads | SOT1275-3 |  |  |  |  |
| BLC8G27LS-60AVH | -      | air cavity plastic earless flanged package; 6 leads | SOT1275-1 |  |  |  |  |

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter            | Conditions | Min  | Max  | Unit |
|------------------|----------------------|------------|------|------|------|
| $V_{DS}$         | drain-source voltage |            | -    | 65   | V    |
| $V_{GS}$         | gate-source voltage  |            | -0.5 | +13  | V    |
| T <sub>stg</sub> | storage temperature  |            | -65  | +150 | °C   |
| Tj               | junction temperature | [1]        | -    | 225  | °C   |

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                  | Parameter                                | Conditions  | Тур  | Unit |
|-------------------------|--|---|------|------|
| R <sub>th(j-case)</sub> | thermal resistance from junction to case | T <sub>case</sub> = 80 °C; I <sub>Dq</sub> = 100 mA;<br>V <sub>GS(amp) peak</sub> = 1 V |      |      |
|                         |  | P <sub>L</sub> = 7 W  | 1.84 | K/W  |
|                         |  | P <sub>L</sub> = 16 W   | 1.25 | K/W  |

#### 6. Characteristics

#### Table 6. DC characteristics

 $T_i$  = 25 °C unless otherwise specified.

| Symbol               | Parameter                        | Conditions  | Min      | Тур  | Max  | Unit |
|----------------------|----------------------------------|---|----------|------|------|------|
| Main dev             | ice                              |   | <u> </u> |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown voltage   | V <sub>GS</sub> = 0 V; I <sub>D</sub> = 0.18 mA               | 65.25    | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 18 mA                | 1.45     | 1.9  | 2.35 | V    |
| $V_{GSq}$            | gate-source quiescent voltage    | V <sub>DS</sub> = 28 V; I <sub>D</sub> = 108 mA               | 1.75     | 2.2  | 2.65 | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V                 | -        | -    | 1.2  | μΑ   |
| I <sub>DSX</sub>     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 3.75 \text{ V}; V_{DS} = 10 \text{ V}$ | -        | 3.2  | -    | Α    |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V                 | -        | -    | 120  | nA   |
| 9 <sub>fs</sub>      | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 18 mA                | -        | 0.16 | -    | S    |
| R <sub>DS(on)</sub>  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V}; I_D = 0.63 \text{ A}$  | -        | 792  | 1260 | mΩ   |
| Peak dev             | ice                              |   |          |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown voltage   | V <sub>GS</sub> = 0 V; I <sub>D</sub> = 0.4 mA                | 65.25    | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 40 mA                | 1.45     | 1.9  | 2.35 | V    |
| $V_{GSq}$            | gate-source quiescent voltage    | V <sub>DS</sub> = 28 V; I <sub>D</sub> = 240 mA               | 1.45     | 1.9  | 2.35 | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V                 | -        | -    | 1.2  | μΑ   |
| I <sub>DSX</sub>     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 3.75 \text{ V}; V_{DS} = 10 \text{ V}$ | -        | 7.0  | -    | Α    |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V                 | -        | -    | 120  | nA   |
| 9 <sub>fs</sub>      | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 40 mA                | -        | 0.4  | -    | S    |
| R <sub>DS(on)</sub>  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V}; I_D = 1.4 \text{ A}$   | -        | 356  | 573  | mΩ   |

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 2496 MHz;  $f_2$  = 2690 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2496 MHz to 2690 MHz.

| Symbol     | Parameter                    | Conditions        | Min  | Тур | Max | Unit |
|------------|------------------------------|-------------------|------|-----|-----|------|
| Gp         | power gain                   | $P_{L(AV)} = 7 W$ | 13.8 | 15  | -   | dB   |
| RLin       | input return loss            | $P_{L(AV)} = 7 W$ | -    | -10 | -7  | dB   |
| $\eta_{D}$ | drain efficiency             | $P_{L(AV)} = 7 W$ | 40   | 44  | -   | %    |
| ACPR       | adjacent channel power ratio | $P_{L(AV)} = 7 W$ | -    | -28 | -23 | dBc  |

#### Table 8. RF characteristics

Test signal: pulsed CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 2690 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2496 MHz to 2690 MHz.

| Symbol              | Parameter                             | Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------------|------------|-----|-----|-----|------|
| P <sub>L(3dB)</sub> | output power at 3 dB gain compression |            | 42  | 50  | -   | W    |

#### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC8G27LS-60AV and BLC8G27LS-60AVH are capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 100 \text{ mA (main)}$ ;  $V_{GS(amp)peak} = 0.5 \text{ V}$ ;  $P_L = 20 \text{ W (CW)}$ ; f = 2496 MHz.

### 7.2 Impedance information

Table 9. Typical impedance of main device Measured load-pull data of main device;  $I_{Dq} = 100 \text{ mA (main)}$ ;  $V_{DS} = 28 \text{ V}$ .

| f           | Z <sub>S</sub> [1]  | Z <sub>L</sub> [1] | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |  |  |  |  |  |
|-------------|---------------------|--------------------|--------------------|--------------------|--------------------|--|--|--|--|--|
| (MHz)       | (Ω)                 | (Ω)                | (W)                | (%)                | (dB)               |  |  |  |  |  |
| Maximum po  | Maximum power load  |                    |                    |                    |                    |  |  |  |  |  |
| 2496        | 6.3 – j11.2         | 18.4 – j12.7       | 23                 | 60                 | 18.8               |  |  |  |  |  |
| 2600        | 8.9 – j12.3         | 17.5 – j12.4       | 23                 | 58                 | 19.1               |  |  |  |  |  |
| 2690        | 10.7 – j9.5         | 16.0 – j12.5       | 22                 | 56                 | 19.4               |  |  |  |  |  |
| Maximum dra | nin efficiency load |                    |                    |                    |                    |  |  |  |  |  |
| 2496        | 6.3 – j11.2         | 28.0 - j0.0        | 17                 | 67.0               | 20.9               |  |  |  |  |  |
| 2600        | 8.9 – j12.3         | 24.4 – j1.7        | 16                 | 65.5               | 21.2               |  |  |  |  |  |
| 2690        | 10.7 – j9.5         | 19.4 – j0.0        | 17                 | 64.5               | 21.3               |  |  |  |  |  |

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device;  $I_{Dq}$  = 240 mA (peak);  $V_{DS}$  = 28 V.

| f          | Z <sub>S</sub> [1] | Z <sub>L</sub> [1] | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |
|------------|--------------------|--------------------|--------------------|--------------------|--------------------|
| (MHz)      | (Ω)                | (Ω)                | (W)                | (%)                | (dB)               |
| Maximum po | wer load           |                    |                    |                    |                    |
| 2496       | 4.5 – j9.9         | 5.8 – j9.8         | 51                 | 55.9               | 17.6               |
| 2600       | 4.7 – j9.8         | 6.0 – j9.7         | 51                 | 56.9               | 18.3               |
| 2690       | 2.5 – j5.3         | 6.6 – j10.4        | 52                 | 57.0               | 17.8               |

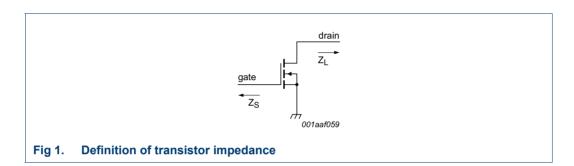
<sup>[2]</sup> at 3 dB gain compression.

Table 10. Typical impedance of peak device ...continued

Measured load-pull data of peak device;  $I_{Dq}$  = 240 mA (peak);  $V_{DS}$  = 28 V.

| f           | Z <sub>S</sub> [1]            | Z <sub>L</sub> [1] | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |  |  |  |  |
|-------------|-------------------------------|--------------------|--------------------|--------------------|--------------------|--|--|--|--|
| (MHz)       | (Ω)                           | (Ω)                | (W)                | (%)                | (dB)               |  |  |  |  |
| Maximum dra | Maximum drain efficiency load |                    |                    |                    |                    |  |  |  |  |
| 2496        | 4.5 – j9.9                    | 11.6 – j5.8        | 36.5               | 64.1               | 20.3               |  |  |  |  |
| 2600        | 4.7 – j9.8                    | 10.2 – j4.6        | 34.4               | 63.3               | 20.7               |  |  |  |  |
| 2690        | 2.5 – j5.3                    | 9.1 – j4.9         | 35.1               | 62.3               | 20.5               |  |  |  |  |

- [1] Z<sub>S</sub> and Z<sub>L</sub> defined in Figure 1.
- [2] at 3 dB gain compression.



### 7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device;  $I_{Da}$  = 100 mA (main);  $V_{DS}$  = 28 V.

| f     | Z <sub>S</sub> [1] | Z <sub>L</sub> [1] | P <sub>L</sub> [2] | η <sub>D</sub> [3] | G <sub>p</sub> [3] |
|-------|--------------------|--------------------|--------------------|--------------------|--------------------|
| (MHz) | (Ω)                | (Ω)                | (dBm)              | (%)                | (dB)               |
| 2496  | 6.3 – j11.2        | 25.0 – j9.2        | 43.2               | 37.0               | 20.0               |
| 2600  | 8.9 – j12.3        | 21.5 – j7.6        | 43.2               | 37.3               | 20.2               |
| 2690  | 10.7 – j9.5        | 20.7 – j8.8        | 43.2               | 37.1               | 20.2               |

- [1]  $Z_S$  and  $Z_L$  defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 38.5 \text{ dBm}$ .

Table 12. Typical impedance of main device at 1: 2.5 load

Measured load-pull data of main device;  $I_{Dq}$  = 100 mA (main);  $V_{DS}$  = 28 V.

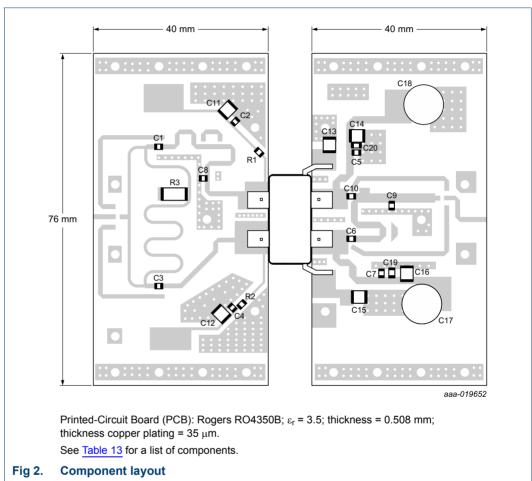
| f     | Z <sub>S</sub> [1] | Z <sub>L</sub> [1] | P <sub>L</sub> [2] | η <sub>D</sub> [3] | G <sub>p</sub> [3] |
|-------|--------------------|--------------------|--------------------|--------------------|--------------------|
| (MHz) | (Ω)                | (Ω)                | (dBm)              | (%)                | (dB)               |
| 2496  | 6.3 – j11.2        | 24.5 – j17.8       | 40.0               | 52.0               | 22.0               |
| 2600  | 8.9 – j12.3        | 18.0 – j11.5       | 40.2               | 51.5               | 22.2               |
| 2690  | 10.7 – j9.5        | 16.9 – j8.2        | 40.6               | 52.1               | 22.0               |

- [1]  $Z_S$  and  $Z_L$  defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 38.5 \text{ dBm}$ .

#### 7.4 VBW in Doherty operation

The BLC8G27LS-60AV and BLC8G27LS-60AVH show 100 MHz (typical) video bandwidth in Doherty demo board in 2600 MHz at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA and  $V_{GS(amp)peak}$  = 0.5 V.

#### 7.5 Test circuit



**Table 13.** List of components
See Figure 2 for component layout.

| Component                       | Description                       | Value           | Remarks  |
|---------------------------------|-----------------------------------|-----------------|----------|
| C1, C2, C3, C4, C5, C6, C7      | multilayer ceramic chip capacitor | 10 pF [1]       | ATC 600F |
| C8, C9                          | multilayer ceramic chip capacitor | 0.2 pF [1]      | ATC 600F |
| C10                             | electrolytic capacitor            | 11 pF [1]       | ATC 600F |
| C11, C12, C13, C14,<br>C15, C16 | multilayer ceramic chip capacitor | 10 μF, 50 V [2] | Murata   |
| C17, C18                        | electrolytic capacitor            | 1000 μF, 100 V  |          |

Table 13. List of components ...continued

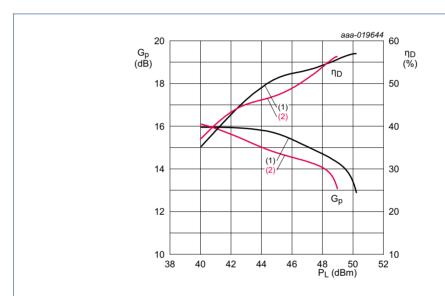
See Figure 2 for component layout.

| Component | Description                       | Value          | Remarks  |
|-----------|-----------------------------------|----------------|----------|
| C19, C20  | multilayer ceramic chip capacitor | 1 μF, 50 V [2] | Murata   |
| R1, R2    | resistor                          | 5.1 Ω          | SMD 0805 |
| R3        | resistor                          | 50 Ω           | SMD 0805 |

- [1] American Technical Ceramics type 600F or capacitor of same quality
- [2] Murata or capacitor of same quality

## 7.6 Graphical data

#### 7.6.1 CW

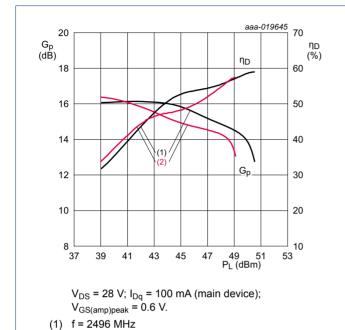


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

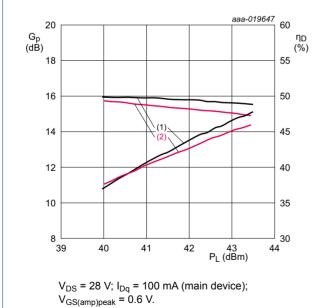
#### 7.6.2 Pulsed CW



- Power gain and drain efficiency as function of output power; typical values
- aaa-019646 25 RLin (dB) 20 15 10 5 0 38 40 42 46 48 50 P<sub>L</sub> (dBm) 52
  - $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);
  - V<sub>GS(amp)peak</sub> = 0.6 V.
  - (1) f = 2496 MHz
  - (2) f = 2690 MHz

Fig 5. Input return loss as a function of output power; typical values

#### 7.6.3 1-Carrier W-CDMA

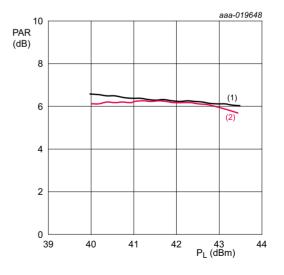


(1) f = 2496 MHz

(2) f = 2690 MHz

(2) f = 2690 MHz

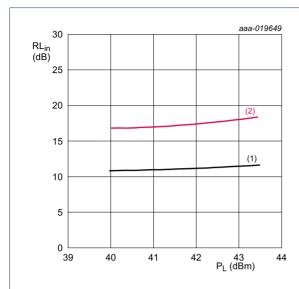
Power gain and drain efficiency as function of Fig 6. output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak} = 0.6 \text{ V}.$ 

- (1) f = 2496 MHz
- (2) f = 2690 MHz

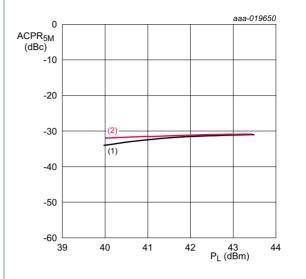
Peak-to-average power ratio as a function of Fig 7. output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 8. Input return loss as a function of output power; typical values

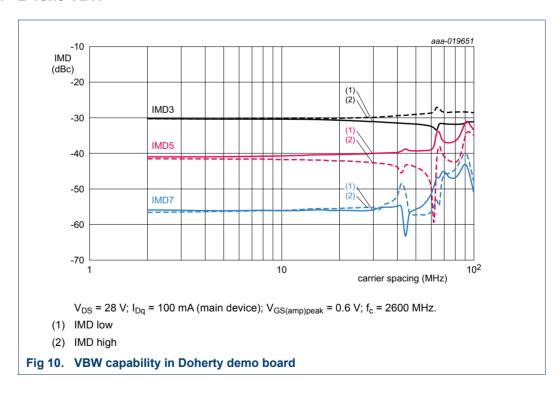


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

#### 7.6.4 2-Tone VBW



## 8. Package outline

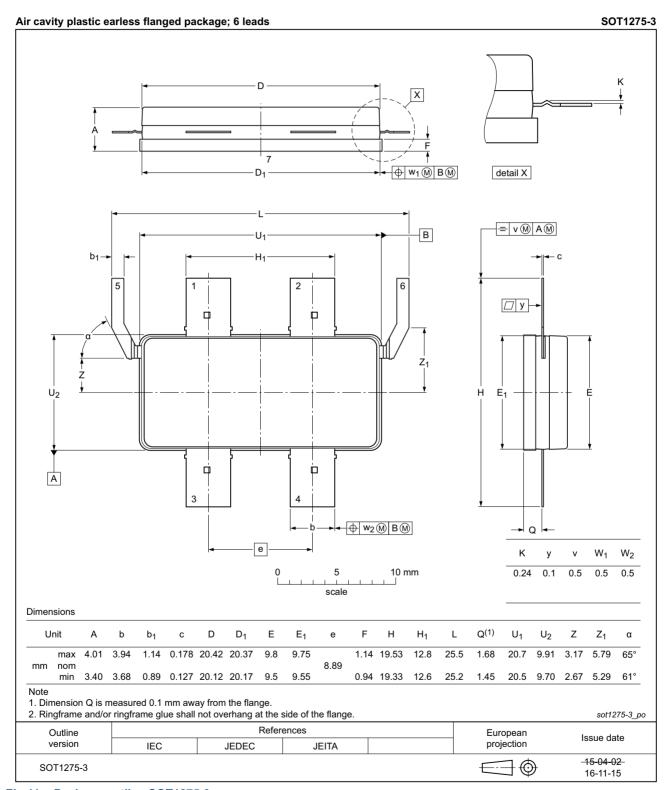


Fig 11. Package outline SOT1275-3

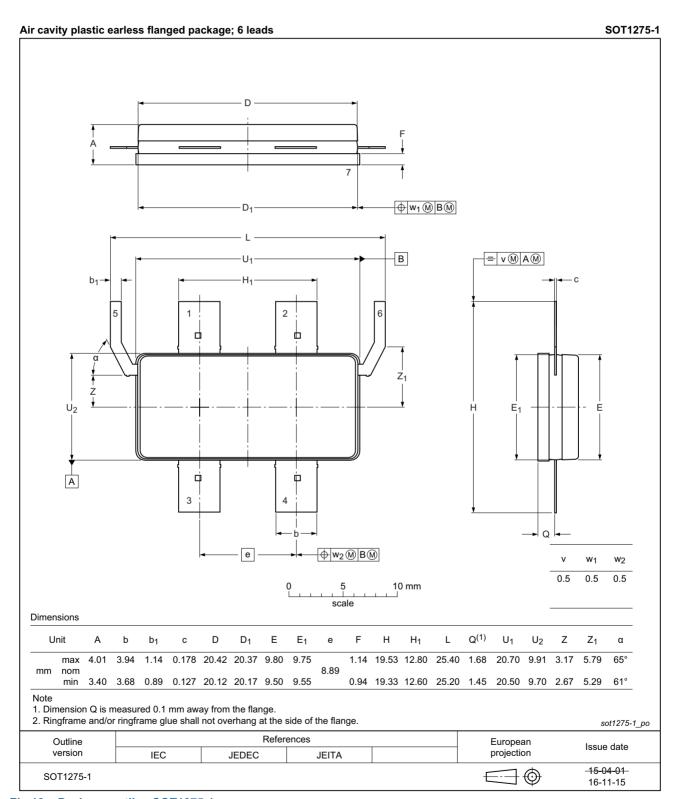


Fig 12. Package outline SOT1275-1

## 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

| ESD model  | Class   |
|--|---------|
| Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002 | C2A [1] |
| Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001     | 0B [2]  |

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 0B is granted to any part that passes after exposure to an ESD pulse of 125 V, but fails after exposure to an ESD pulse of 250 V.

#### 10. Abbreviations

Table 15. Abbreviations

| Acronym | Description                                    |
|---------|--|
| 3GPP    | 3rd Generation Partnership Project             |
| CCDF    | Complementary Cumulative Distribution Function |
| CW      | Continuous Wave                                |
| DPCH    | Dedicated Physical CHannel                     |
| ESD     | ElectroStatic Discharge                        |
| IS-95   | Interim Standard 95                            |
| LDMOS   | Laterally Diffused Metal-Oxide Semiconductor   |
| LTE     | Long Term Evolution                            |
| MTF     | Median Time to Failure                         |
| PAR     | Peak-to-Average Ratio                          |
| SMD     | Surface Mounted Device                         |
| VBW     | Video BandWidth                                |
| VSWR    | Voltage Standing Wave Ratio                    |
| W-CDMA  | Wideband Code Division Multiple Access         |

## 11. Revision history

#### Table 16. Revision history

| Document ID                   | Release date  | Data sheet status      | Change notice      | Supersedes                        |
|-------------------------------|---|------------------------|--------------------|-----------------------------------|
| BLC8G27LS-60AV_27LS-60AVH v.4 | 20161202  | Product data sheet     | -                  | BLC8G27LS-60AV_27LS-<br>60AVH v.3 |
| Modifications:                | Figure 11 on page 10: updated package outline drawing SOT1275-3 |                        |                    |                                   |
|                               | • <u>Figure 12 o</u>  | n page 11: updated pac | kage outline drav  | ving SOT1275-1                    |
|                               | Section 9 o   | n page 12: updated Har | ndling information |                                   |
| BLC8G27LS-60AV_27LS-60AVH v.3 | 20160408  | Product data sheet     | -                  | BLC8G27LS-60AV_27LS-<br>60AVH v.2 |
| BLC8G27LS-60AV_27LS-60AVH v.2 | 20151027  | Product data sheet     | -                  | BLC8G27LS-60AV v.1                |
| BLC8G27LS-60AV v.1            | 20150330  | Objective data sheet   | -                  | -                                 |

## 12. Legal information

#### 12.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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BLC8G27LS-60AV 27LS-60AVH

## BLC8G27LS-60AV(H)

#### **Power LDMOS transistor**

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## **AMPLEON**

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**Power LDMOS transistor** 

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